

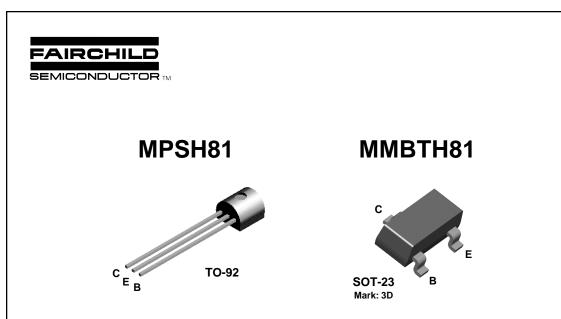
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PNP RF Transistor

This device is designed for general RF amplifier and mixer applications to 250 mHz with collector currents in the 1.0 mA to 30 mA range. Sourced from Process 75.

Absolute Maximum Ratings* TA = 25°C unless otherwise noted

| Symbol | Parameter | Value | Units |
|-----------------------------------|--|-------------|-------|
| V _{CEO} | Collector-Emitter Voltage | 20 | V |
| V _{CBO} | Collector-Base Voltage | 20 | V |
| V _{EBO} | Emitter-Base Voltage | 3.0 | V |
| I _C | Collector Current - Continuous | 50 | mA |
| T _J , T _{stg} | Operating and Storage Junction Temperature Range | -55 to +150 | °C |

*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES:

1) These ratings are based on a maximum junction temperature of 150 degrees C.
2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.
3) All voltages (V) and currents (A) are negative polarity for PNP transistors.

Thermal Characteristics TA = 25°C unless otherwise noted

| Symbol | Characteristic | Мах | | Units |
|---------------------|---|------------|------------|-------------|
| | | MPSH81 | *MMBTH81 | |
| P _D | Total Device Dissipation Derate above 25°C | 350 2.8 | 225 1.8 | mW mW/∘C |
| $R_{\theta JC}$ | Thermal Resistance, Junction to Case | 125 | | °C/W |
| $R_{	ext{	hetaJA}}$ | Thermal Resistance, Junction to Ambient | 357 | 556 | °C/W |

*Device mounted on FR-4 PCB 1.6" X 1.6" X 0.06."

PNP RF Transistor

 $I_{C} = 10 I_{E}$

- 100

-10

| (cor | ntin | ued) | |
|------|------|------|--|
| (00. | | | |

| Electrical Characteristics TA = 25°C unless otherwise noted | | | | | | |
|---|--------------------------------------|---------------------------------------|-----|-----|-------|--|
| Symbol | Parameter | Test Conditions | Min | Max | Units | |
| OFF CHARACTERISTICS | | | | | | |
| V _{(BR)CEO} | Collector-Emitter Breakdown Voltage* | $I_{\rm C} = 1.0$ mA, $I_{\rm B} = 0$ | 20 | | V | |
| | Collector-Base Breakdown Voltage | $ _{c} = 10 \text{ µA}, _{E} = 0$ | 20 | | V | |

| (=) = = = | 0 | | | | |
|----------------------|----------------------------------|-------------------------------------|-----|-----|----|
| V _{(BR)CBO} | Collector-Base Breakdown Voltage | $I_{C} = 10 \ \mu A, \ I_{E} = 0$ | 20 | | V |
| V _{(BR)EBO} | Emitter-Base Breakdown Voltage | $I_{E} = 10 \ \mu A, \ I_{C} = 0$ | 3.0 | | V |
| I _{CBO} | Collector Cutoff Current | $V_{CB} = 10 \text{ V}, I_{E} = 0$ | | 100 | nA |
| I _{EBO} | Emitter Cutoff Current | $V_{EB} = 2.0 \text{ V}, I_{C} = 0$ | | 100 | nA |

ON CHARACTERISTICS

| h _{FE} | DC Current Gain | $I_{C} = 5.0 \text{ mA}, V_{CE} = 10 \text{ V}$ | 60 | | |
|----------------------|--------------------------------------|--|----|-----|---|
| V _{CE(sat)} | Collector-Emitter Saturation Voltage | $I_{C} = 5.0 \text{ mA}, I_{B} = 0.5 \text{ mA}$ | | 0.5 | V |
| V _{BE(on)} | Base-Emitter On Voltage | $I_{C} = 5.0 \text{ mA}, V_{CE} = 10 \text{ V}$ | | 0.9 | V |

SMALL SIGNAL CHARACTERISTICS

| f _T | Current Gain - Bandwidth Product | $I_{C} = 5.0 \text{ mA}, V_{CE} = 10 \text{ V},$ f = 100 MHz | 600 | | MHz |
|-----------------|----------------------------------|---|-----|------|-----|
| C _{cb} | Collector-Base Capacitance | $V_{CB} = 10 \text{ V}, I_E = 0, f = 1.0 \text{ MHz}$ | | 0.85 | pF |
| C _{ce} | Collector Emitter Capcitance | $V_{CB} = 10 \text{ V}, I_B = 0, f = 1.0 \text{ MHz}$ | | 0.65 | pF |

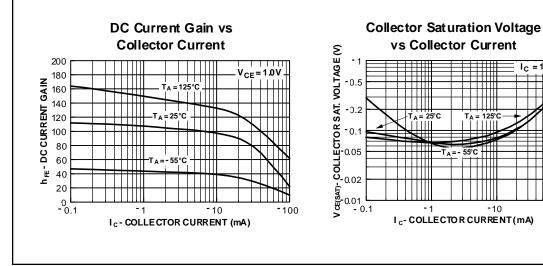
*Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%

NOTE: All voltages (V) and currents (A) are negative polarity for PNP transistors.

Spice Model

PNP(Is=10f Xti=3 Eg=1.11 Vaf=100 Bf=133.8 Ise=1.678p Ne=2.159 Ikf=.1658 Nk=.901 Xtb=1.5 Var=100 Br=1 Isc=9.519n Nc=3.88 Ikr=5.813 Rc=7.838 Cjc=2.81p Mjc=.1615 Vjc=.8282 Fc=.5 Cje=2.695p Mje=.3214 Vje=.7026 Tr=11.32n Tf=97.83p Itf=69.29 Xtf=599u Vtf=10)

Typical Characteristics



MPSH81 / MMBTH81

MPSH81 / MMBTH81 **PNP RF Transistor** (continued) **Typical Characteristics** (continued) Base-Emitter ON Voltage **Base-Emitter Saturation NOLTAGE (V)** vs Collector Current Voltage vs Collector Current V BEOM- BASE-EMITTER ON VOLTAGE (V) 0-0 0-0 700 - 0 7000 - 0 7000 - 0 7000 - 0 7000 - 0 7000 - 0 7000 - 0 7000 - 0 7000 - 0 7000 - 0 7000 - 0 70000 70 V_{CE} = 10V $I_{\rm C} = 10 I_{\rm B}$ T_A = 25°C **1.**2 ŦĦ -1 -0.8 -0.6 T_A = 100°C †††† а-(_{мс})-04 -0-04 Л Γ_Δ = 125 0 - 0.1 **-**0.1 -100 -1 -10 I^C- COLLECTOR CURRENT (mA) -10 -100 Ic - COLLECTOR CURRENT (mA) Input / Output Capacitance **Collector Reverse Current** I ces- COLLECTOR REVERSE CURRENT (IA) vs Ambient Temperature vs Reverse Bias Voltage 3 100 = 1.0 MHz 2.8 **CAPACITANCE (pF)** 2.2 2.2 2.2 1.8 1.6 1.6 10 V_{CE}=-6.0V Cobo V_{CE}=-3.0V 0.1 1.4 Ċibo 1.2 1 25 50 75 100 150 125 0 -2 -4 -6 -8 -10 T_A - AMBIENT TEMPERATURE (°C) **REVERSE BIAS VOLTAGE (V) Contours of Constant Gain Power Dissipation vs** Ambient Temperature Bandwidth Product (f_T) 350 TO-92 -8 SOT-23 1500 MHz 1200 MH -6 500 MHz 200 MH -2 500 MHz 200 MH 900 MHz _ ل_ - 0.1 0 -10 -100 - 1 50 75 100 TEMPERATURE (°C) 0 25 125 150 Ic- COLLECTOR CURRENT (mA)



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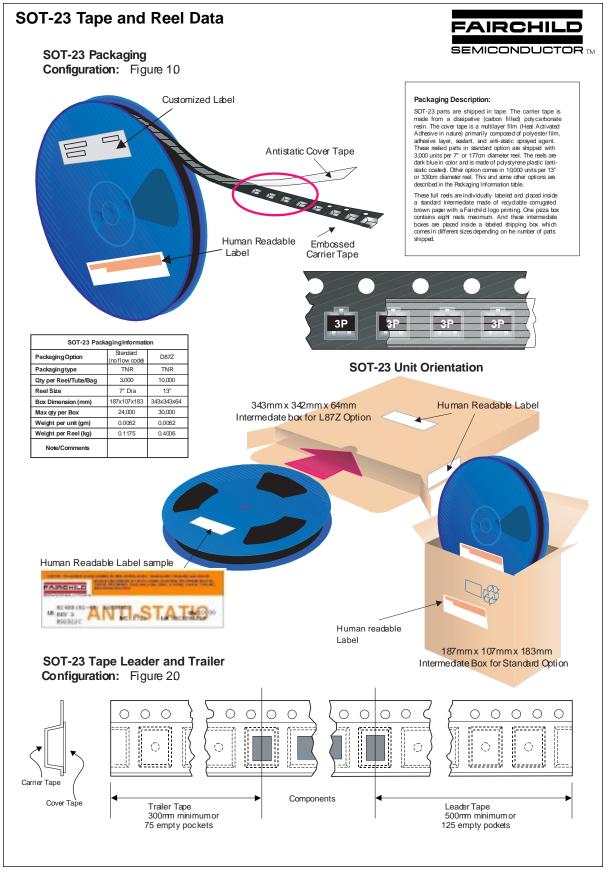
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September 1999, Rev. C

